

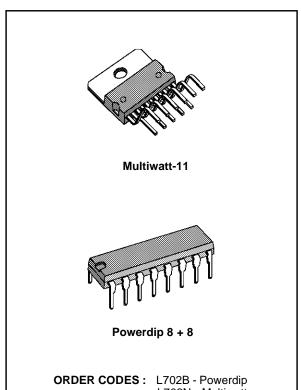
2A QUAD DARLINGTON SWITCH

- SUSTAINING VOLTAGE: 70 V
- 2 A OUTPUT
- HIGH CURRENT GAIN
- IDEAL FOR DRIVING SOLENOIDS, DC MOTORS, STEPPER MOTORS, RELAYS, DISPLAYS, ETC.



The L702 is a monolithic integrated circuit for high current and high voltage switching applications. It comprises four darlington transistors with common emitter and open collector suitable for current sinking applications mounted on the new POWERDIP and Multiwatt® packages.

This circuit reduces components, sizes and costs; it can provide direct interface between low level logic and a variety of high current applications.



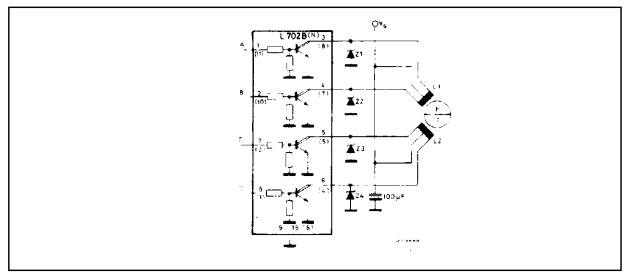
L702N - Multiwatt

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit		
V _{CEX}	Collector-emitter Voltage (input open)			90	V
Vi	Input Voltage	30	V		
Ic	Collector Current			3	Α
P _{tot}	Total Power Dissipation at T_{pin} 9 to 16 \leq 90 $^{\circ}C$	}	Powerdip	4	W
	Total Power Dissipation at T _{amb} ≤ 70 °C	j rowerdip		1.1	W
	Total Power Dissipationa tT _{case} ≤ 90 °C		Multiwatt	20 W	
T _{stg}	Storage Temperature			-55 to 150	°C
Tj	Operating Junction Temperature			-25 to 150	°C

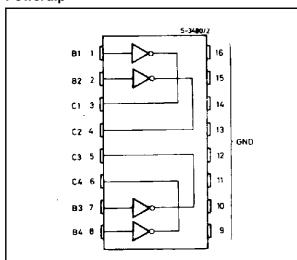
October 1991 1/7

STEPPING MOTOR BUFFER

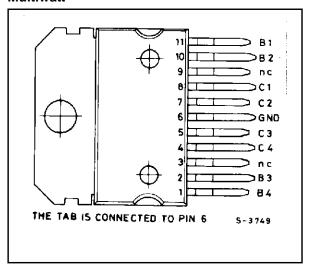


CONNECTION DIAGRAMS (top view)

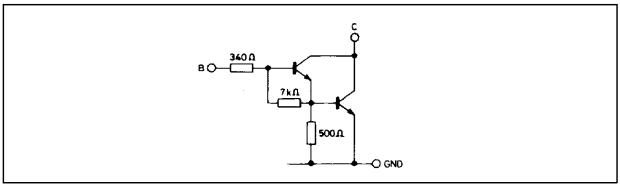
Powerdip



Multiwatt



SCHEMATIC DIAGRAM (each Darlington)



THERMAL DATA

Symbol	Parameter			Value	Unit
R _{th j-amb}	Thermal Resistance Junction Ambient	} Powerdip	Max	70	°C/W
R _{th j-pins 9/16}	Thermal Resistance Junction Pins 9 to 16) Toweraip	Max	14	°C/W
R _{th j-case}	Thermal Resistance Junction-case	Multiwatt	Max	3	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise specified)

Symbol	Param	neter	Test c	Min.	Тур.	Max.	Unit	
I _{CEX}	Output Leakage	Current	V _{CE} = 90 V	V _{CE} = 90 V		10	50	μΑ
V _{CE(sust)}	Collector Emitter Voltage	(°) Sustaining	I _C = 100 mA		70			V
V _{CE(sat)}	Collector Emitter Voltage	Saturation	I _C = 1.25 A I _i = 2 mA			1.3	1.9	V
h _{FE}	DC Forward Cur	rent Gain	I _C = 1 A V _{CE} = 3 V		1.000	4.000		
li	Input Current		V _i = 3.75 V V _i = 2.4 V Open Collector			7 3	11 6	mA mA
Vi	Input Voltage	Off Condition	V _{CE} = 70 V	$I_C \le 0.1 \text{ mA}$			0.4	V
		On Condition	V _{CE} = 3 V	I _C ≥ 1 A	2.4			V
Ton	Turn On Time		V _s = 12 V			0.3		μs
T _{off}	Turn Off Time		$R_L = 10 \Omega$			1		μs

Figure 1. Switching Time.

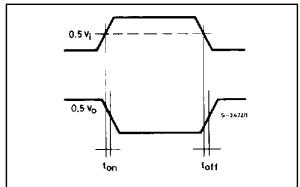


Figure 2. ton and toff Test Circuit.

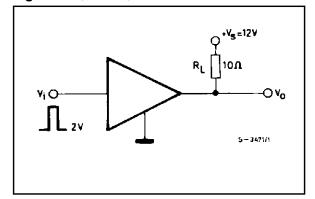


Figure 3. Peak Collector Current vs. Duty Cycle and Number of Outputs (L702B only)

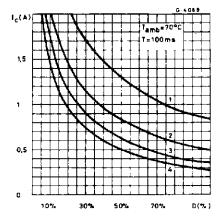


Figure 5. Collector Current vs. Input Voltage.

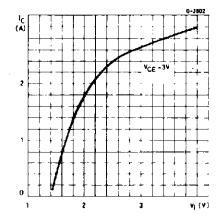


Figure 7. Safe Operating Areas (L702B).

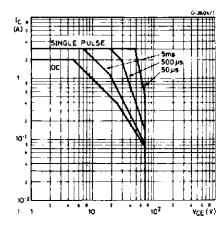


Figure 4. Collector Emitter Saturation Voltage vs. Collector Current.

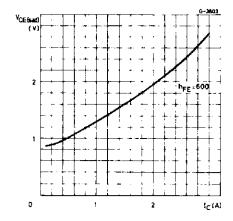


Figure 6. Input Current vs. Input Voltage.

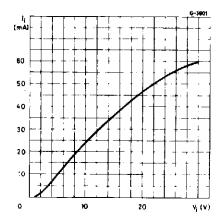
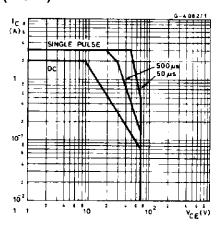
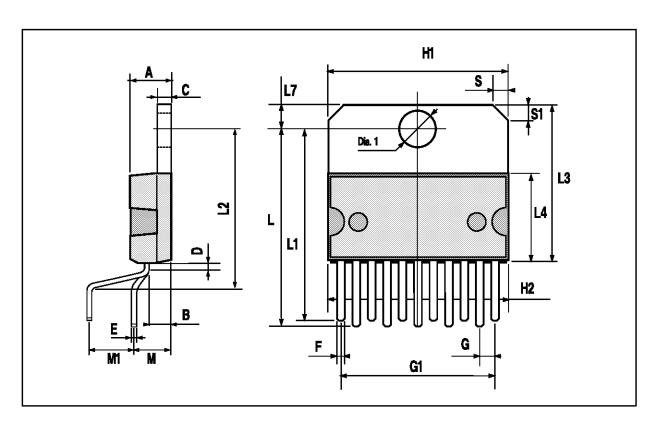


Figure 8. Safe Operating Areas (L702N).



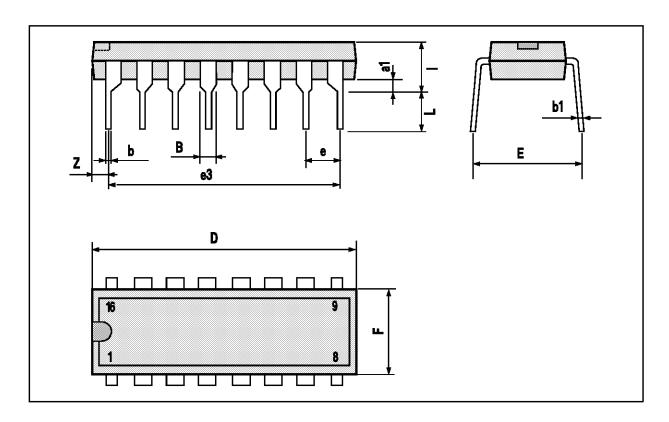
MULTIWATT11 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			5			0.197
В			2.65			0.104
С			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.88		0.95	0.035		0.037
G	1.57	1.7	1.83	0.062	0.067	0.072
G1	16.87	17	17.13	0.664	0.669	0.674
H1	19.6			0.772		
H2			20.2			0.795
L	21.5		22.3	0.846		0.878
L1	21.4		22.2	0.843		0.874
L2	17.4		18.1	0.685		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
М	4.1	4.3	4.5	0.161	0.169	0.177
M1	4.88	5.08	5.3	0.192	0.200	0.209
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152



POWERDIP PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			20.0			0.787
Е		8.80			0.346	
е		2.54			0.100	
e3		17.78			0.700	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050



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